GLF71300, GLF71301, GLF71302 GLF71303, GLF71306, GLF71308 Nano-Current Consumed, I_QSmart[™] Power Load Switch with Slew Rate Control

DESCRIPTION

The GLF7130x is an ultra-efficiency, 2.0 A rated, Load Switch with integrated slew rate control. The best in class efficiency makes it an ideal choice for use in IoT, mobile, and wearable electronics.

The GLF7130x features an ultra-efficient I_QSmart^{TM} technology that supports the lowest quiescent current (I_Q) and shutdown current (I_{SD}) in the industry. Low I_Q and I_{SD} solutions help designers to reduce parasitic leakage current, improve system efficiency, and increase battery lifetime.

The GLF7130x integrated slew rate control can also enhance system reliability by mitigating bus voltage swings during switching events. Where uncontrolled switches can generate high inrush currents that result in voltage droop and/or bus reset events, the GLF7130x slew rate control specifically limits inrush current during turn-on to minimize voltage droop.

The GLF7130x Load Switch device supports an industry leading wide input voltage range and helps to improve operating life and system robustness. Furthermore, one device can be used in multiple voltage rail applications which helps to simplify inventory management and reduces operating cost.

The GLF7130x Load Switch device is small utilizing a wafer level chip scale package with 4 bumps in a 0.77 mm x 0.77 mm x 0.46 mm die size and a 0.4 mm bump pitch.

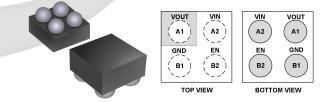
FEATURES

- Ultra-Low I_Q: 1 nA Typ at 5.5 V_{IN} on GLF71300, GLF71301, GLF71306, GLF71308
 - 540 nA Typ at 5.5 V_{IN} on GLF71302, GLF71303
- Ultra-Low I_{SD} : 19 nA Typ at 5.5 V_{IN}
- Low R_{ON} = 34 m Ω Typ. at 5.5 V_{IN}
- I_{OUT} Max = 2.0 A
- Wide Input Range: 1.1 V to 5.5 V
 - 6 Vabs max
- Controlled Rise Time: 430 μs at 3.3V_{IN}: GLF71300, GLF71301,
 - GLF71302, GLF71303
 - 42 µs at 3.3V_{IN}: GLF71306, GLF71308
- Internal EN Pull-Down Resistor on GLF71300, GLF71301, GLF71306, GLF71308
- Internal EN Pull-Up Resistor on GLF71302 and GLF71303
- Integrated Output Discharge Switch: GLF71301, GLF71303, GLF71308
- Ultra-Small: 0.77 mm x 0.77 mm

APPLICATIONS

- Wearables
- Data Storage, SSD
- Mobile Devices
- Low Power Subsystems

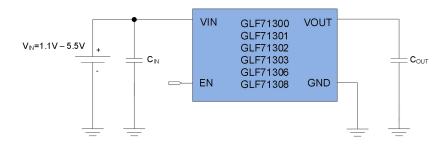
PACKAGE



0.77 mm x 0.77 mm x 0.46 mm WLCSP

INTEGRATED POWER Nano-Current Consumed, I_QSmart[™] Power Load Switch with Slew Rate Control

APPLICATION DIAGRAM



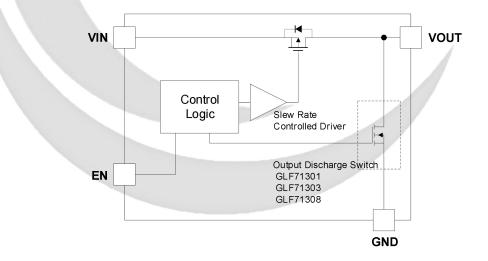
ALTERNATE DEVICE OPTIONS

Part Number	Top Mark	Vout Rise Time at 3.3Vin (Typ)	R _{оN} (Тур) at 5.5 V	Output Discharge	EN Activity	Package			
GLF71300	А	430 µs		NA	High				
GLF71301	В	430 µs		85 Ω	підп				
GLF71302	С	430 µs	24	NA	Low	0.77 mm x 0.77 mm			
GLF71303	D	430 µs	34 mΩ	85 Ω	Low	x 0.46 mm WLCSP			
GLF71306	К	42 µs		NA	Llink				
GLF71308	L	42 µs		85 Ω	High				

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FUNCTIONAL BLOCK DIAGRAM

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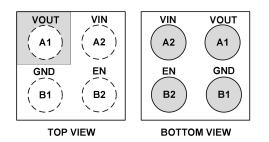


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PIN CONFIGURATION



PIN DEFINITION

Pin #	Name	Description
A1	VOUT	Switch Output
A2	VIN	Switch Input. Supply Voltage for IC
B1	GND	Ground
B2	EN	Enable to control the switch. The EN pin has an internal pull-down resistor for GLF71300, GLF71301, GLF71306, GLF71308, and pull-up for GLF71302 and GLF71303.

Figure 2. 0.77 mm x 0.77 mm x 0.46 mm WLCSP

ABSOLUTE MAXIMUM RATINGS

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions; extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Pa	Min.	Max.	Unit	
V _{IN} , V _{OUT} , V _{EN}	Each Pin Voltage Range to GND	-0.3	6	V	
Ι _{ουτ}	Maximum Continuous Switch Current		2	А	
PD	Power Dissipation at $T_A = 25 \text{ °C}$	$\mathbf{V}\mathbf{V}$	1	W	
Тѕтб	Storage Junction Temperature	-65	150	°C	
T _A	Operating Temperature Range	-40	85	°C	
θ _{JA}	Thermal Resistance, Junction to Ambi		110	°C/W	
ESD	Elestrestatia Discharge Canability	Human Body Model, JESD22-A114	6	kV	
ESD	Electrostatic Discharge Capability Charged Device Model, JESD22-C101		2		ĸν

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min.	Max.	Unit
VIN	Supply Voltage	1.1	5.5	V
TA	Ambient Operating Temperature	-40	+85	°C

Nano-Current Consumed, I_QSmart[™] Power Load Switch with Slew Rate Control

ELECTRICAL CHARACTERISTICS

Values are at V_{IN} = 3.3 V and T_A = 25 °C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Basic Ope	eration					
V _{IN}	Supply Voltage		1.1		5.5	V
	Quiescent Current (1)	V _{IN} = V _{EN} =5.5 V, I _{OUT} =0 mA		1		
lq	GLF71300, GLF71301, GLF71306, GLF71308	V_{IN} = V_{EN} =5.5 V, I_{OUT} =0 mA, Ta=85 °C $^{(5)}$		12		nΔ
IQ	Quiescent Current on	V _{IN} =5.5 V, V _{EN} =0 V, I _{OUT} =0 mA		540		_ nA
	GLF71302, GLF71303	V _{IN} =5.5 V, V _{EN} =0 V, I _{OUT} =0 mA, Ta=85 °C ⁽⁵⁾		620		
		EN = Disable, I _{OUT} =0 mA, V _{IN} =1.1 V		3		
		EN = Disable, I _{OUT} =0 mA, V _{IN} =1.8 V		4		-
		EN = Disable, I_{OUT} =0 mA, V_{IN} =3.3 V		6		
I _{SD}	Shutdown Current	EN = Disable, I_{OUT} =0 mA, V_{IN} =4.5 V		9		nA
		EN = Disable, I _{OUT} =0 mA, V _{IN} =5.5 V		19	50	
		EN = Disable, I _{OUT} =0 mA, V _{IN} =5.5 V, Ta=55 °C ⁽⁵⁾		110		
		EN = Disable, I_{OUT} =0 mA, V_{IN} =5.5V, Ta=85 °C ⁽⁵⁾		600		
		Ta=25 °C		34	47	
		V _{IN} =5.5 V, I _{OUT} = 500 mA Ta=85 °C ⁽⁵⁾		40		
		V _{IN} =3.3 V, I _{OUT} = 500 mA		42	56	
Ron	On-Resistance	Ta=85 °C (3)		50		mΩ
		V _{IN} =1.8 V, I _{OUT} = 300 mA Ta=25 °C		68		-
		V _{IN} =1.2 V, I _{OUT} = 100 mA Ta=25 °C		125		
_		V _{IN} =1.1 V, I _{OUT} = 100 mA Ta=25 °C		155		
R _{DSC}	Output Discharge Resistance	EN=Low , I _{FORCE} = 10 mA for GLF71302, GLF71303 EN=High , I _{FORCE} = 10 mA except GLF71302, GLF71303	70	85	100	Ω
	EN Input Logic High	V _{IN} =1.1 V - 1.8 V	0.9			V
VIH	Voltage	V _{IN} =1.8 V - 5.5 V	1.2			V
	EN Input Logic Low Voltage	V _{IN} =1.1 V - 1.8 V	1		0.3	V
VIL		V _{IN} =1.8 V - 5.5 V	1		0.4	V
R _{EN}	EN Internal resistance	Internal Pull-down Resistance: GLF71300, GLF71301, GLF71306, GLF71308 Internal Pull-up Resistance: GLF71302, GLF71303	7	10.1	13	MΩ
I _{EN}	EN Current (2)	EN=5.5 V			0.8	μA
Switching	Characteristics: GLF7130	00, GLF71301, GLF71302, GLF71303 ⁽³⁾	1	1	.1	
t _{dON}	Turn-On Delay	RL=150 Ω, C _{OUT} =0.1 μF		275		
t _R	V _{OUT} Rise Time	$-R_L - 150 \Omega, C_{OUT} - 0.1 \mu F$		430		
t _{dON}	Turn-On Delay (5)			245		
t _R	VOUT Rise Time (5)	RL=500 Ω, Cout=0.1 μF		410		
t _{dOFF}	Turn-Off Delay (4,5)	R _L =10 Ω, C _{OUT} =0.1 μF		0.38		
t⊦	Vout Fall Time (4,5)	GLF71301, GLF71303		1.32		
t _{dOFF}	Turn-Off Delay ⁽⁵⁾	R _L =10 Ω, C _{OUT} =0.1 μF		0.35		μs
t _F	V _{OUT} Fall Time ⁽⁵⁾	GLF71300, GLF71302 : No Output Discharge, R _{DSC}		2.3		
t _{dOFF}	Turn-Off Delay ^(4,5)	RL=500 Ω, C _{OUT} =0.1 μF		1.1		
t _F	V _{OUT} Fall Time ^(4,5)	GLF71301, GLF71303		18		-
	Turn-Off Delay ⁽⁵⁾	R _L =500 Ω, C _{OUT} =0.1 μF		5.0		
NUCEE		$_{\text{L}}$ GLF71300, GLF71302 : No Output Discharge, R _{DSC}		0.0		-

► ► Nano-Current Consumed, I_QSmartTM Power Load Switch with Slew Rate Control

Switchin	g Characteristics: GLF7130	6, GLF71308 ⁽³⁾		
t _{dON}	Turn-On Delay		32	
t _R	V _{OUT} Rise Time	- R _L =150 Ω, C _{OUT} =0.1 μF	42	
t _{dON}	Turn-On Delay ⁽⁵⁾		32	
t _R	V _{OUT} Rise Time ⁽⁵⁾	- R _L =500 Ω, C _{OUT} =0.1 μF	40	
t_{dOFF}	Turn-Off Delay (5)	R _L =150 Ω, C _{OUT} =0.1 μF	2	
t⊧	Vout Fall Time (5)	GLF71306 : No Output Discharge, R _{DSC}	32	
t_{dOFF}	Turn-Off Delay (4,5)		1	μs
t _F	V _{OUT} Fall Time ^(4,5)	- R _L =150 Ω, C _{OUT} =0.1 μF, GLF71308	13	
\mathbf{t}_{dOFF}	Turn-Off Delay (5)	R _L =500 Ω, C _{OUT} =0.1 μF	4.6	
t _F	V _{OUT} Fall Time ⁽⁵⁾	GLF71306 : No Output Discharge, R _{DSC}	97	
t_{dOFF}	Turn-Off Delay (4,5)		1	
t _F	V _{OUT} Fall Time ^(4,5)	R _L =500 Ω, C _{OUT} =0.1 μF, GLF71308	17	
Notes:	1. I _Q of GLF71300, GLF7130 ²	I, GLF71306, and GLF71308 does not include the EN pin curre	ent through the pull-down res	istor R _{PD.}

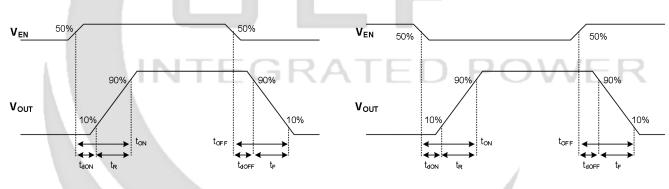
I_Q of GLF71300, GLF71301, GLF71306, and GLF71308 does not include the EN pin current through the pull-down resistor R_{PD}.
 I_{EN} applies only for GLF71300, GLF71301, GLF71306, and GLF71308 with the active high EN pin.

 $t_{ON} = t_{dON} + t_R, t_{OFF} = t_{dOFF} + t_F$ 3.

4. Output discharge path is enabled during off.

5. By design; characterized, not production tested.

TIMING DIAGRAM



GLF71300, GLF71301, GLF71306, GLF71308

GLF71302, GLF71303

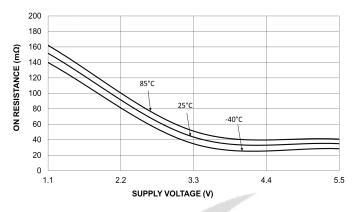
Figure 3. Timing Diagram

Nano-Current Consumed, I_QSmart[™] Power Load Switch with Slew Rate Control

TYPICAL PERFORMANCE CHARACTERISTICS

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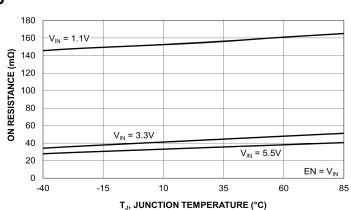
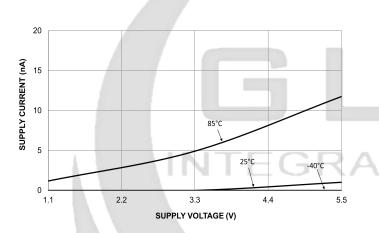
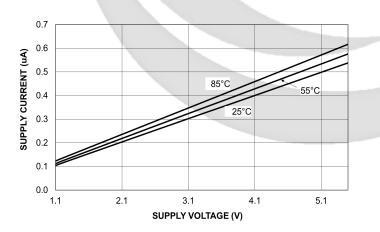


Figure 4. On-Resistance vs. Supply Voltage







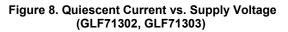


Figure 5. On-Resistance vs. Temperature

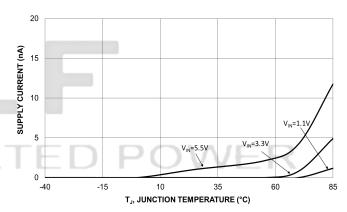
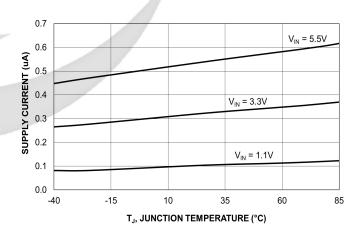
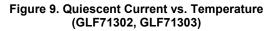


Figure 7. Quiescent Current vs. Temperature (GLF71300, GLF71301, GLF71306, GLF71308)





► **Nano-Current Consumed, I**QSmartTM Power Load Switch with Slew Rate Control INTEGRATED POWER

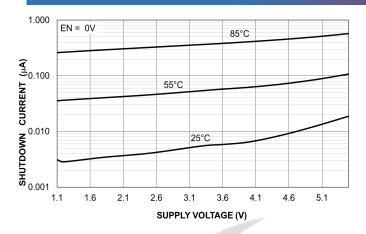


Figure 10. Shutdown Current vs. Supply Voltage

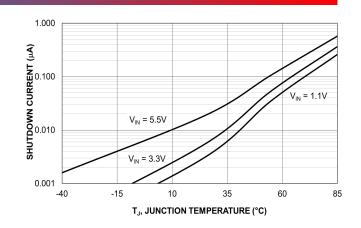


Figure 11. Shutdown Current vs. Temperature

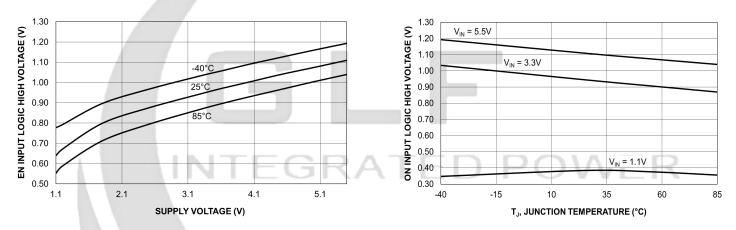


Figure 12. EN Input Logic High Threshold

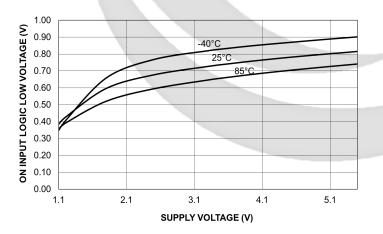


Figure 14. EN Input Logic Low Threshold

Figure 13. EN Input Logic High Threshold Vs. Temperature

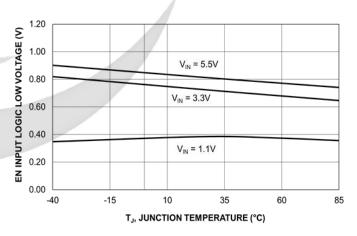
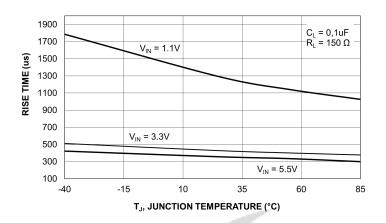
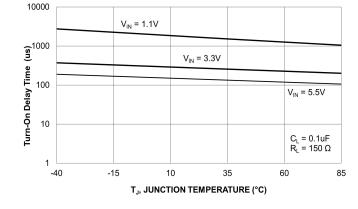
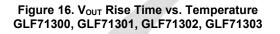


Figure 15. EN Input Logic Low Threshold Vs. Temperature

► ► Nano-Current Consumed, I_QSmartTM Power Load Switch with Slew Rate Control







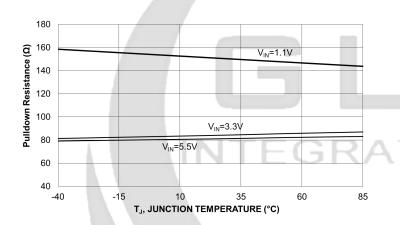


Figure 18. Pull-down Resistance vs. Temperature

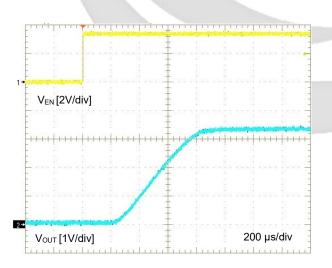
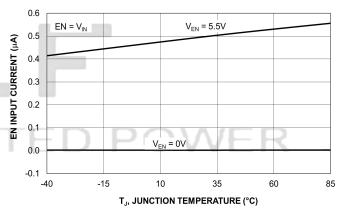




Figure 17. Turn-On Delay Time vs. Temperature GLF71300, GLF71301, GLF71302, GLF71303





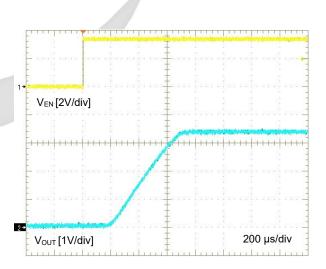
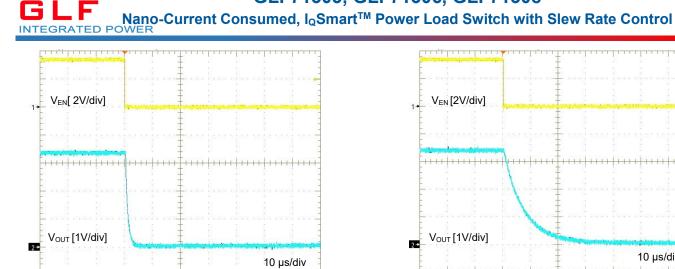
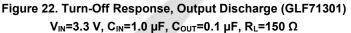


Figure 21. Turn-On Response (GLF71301) V_{IN}=3.3 V, C_{IN}=1.0 μF, C_{OUT}=0.1 μF, R_L=500 Ω





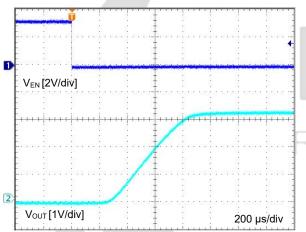
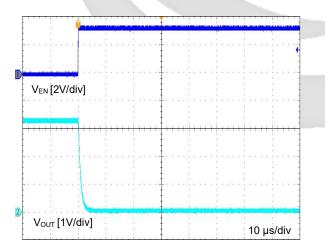
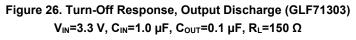


Figure 24. Turn-On Response (GLF71303) VIN=3.3 V, CIN=1.0 μF, COUT=0.1 μF, RL=150 Ω





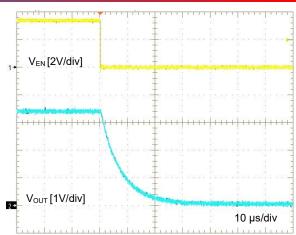


Figure 23. Turn-Off Response, Output Discharge (GLF71301) VIN=3.3 V, CIN=1.0 μF, COUT=0.1 μF, RL=500 Ω

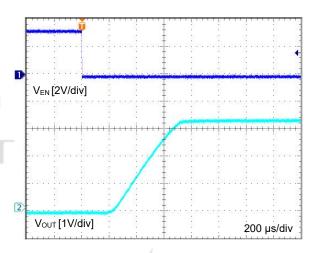
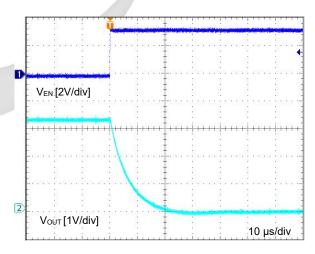
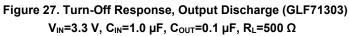
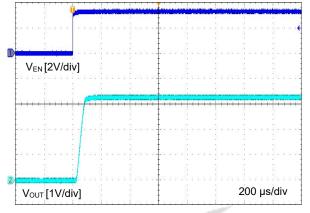


Figure 25. Turn-On Response (GLF71303) V_{IN}=3.3 V, C_{IN}=1.0 μF, C_{OUT}=0.1 μF, R_L=500 Ω

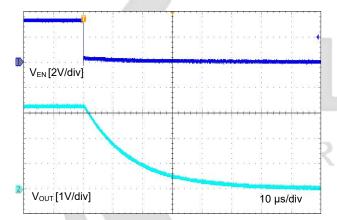


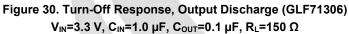


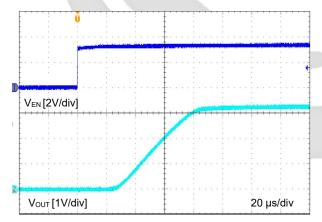
GLF Nano-Current Consumed, I_QSmart[™] Power Load Switch with Slew Rate Control

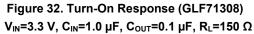












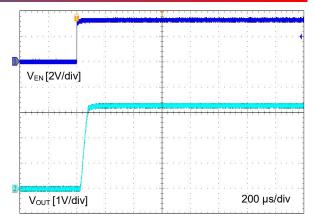


Figure 29. Turn-On Response (GLF71306) V_{IN}=3.3 V, C_{IN}=1.0 \ \mu\text{F}, C_{OUT}=0.1 \ \mu\text{F}, R_L=500 \ \Omega

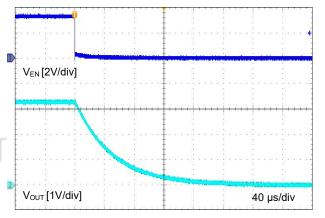


Figure 31. Turn-Off Response, Output Discharge (GLF71306) V_{IN} =3.3 V, C_{\text{IN}} =1.0 μF , C_{OUT}=0.1 μF , R_L=500 Ω

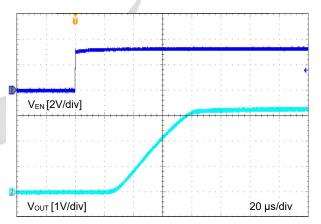
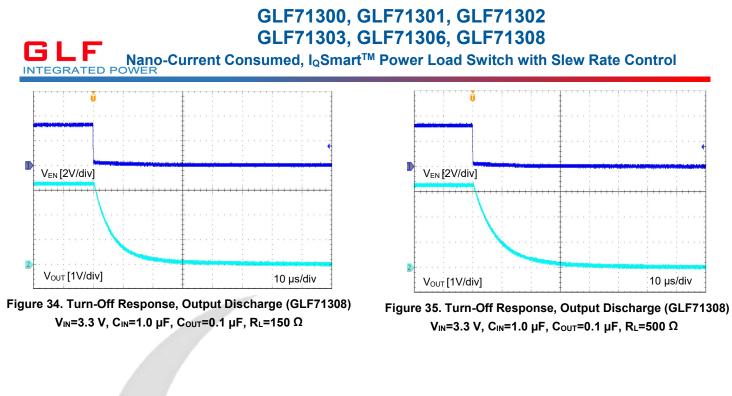


Figure 33. Turn-On Response (GLF71308) V_{IN}=3.3 V, C_{IN}=1.0 \ \mu\text{F}, C_{OUT}=0.1 \ \mu\text{F}, R_{L}=500 \ \Omega





GLF71300, GLF71301, GLF71302

GLF71303, GLF71306, GLF71308

► ► Nano-Current Consumed, I_QSmart[™] Power Load Switch with Slew Rate Control INTEGRATED POWER

APPLICATION INFORMATION

The GLF7130x family of devices are integrated 2.0 A, Ultra-Efficient I₀Smart[™] Load Switch devices with a fixed slew rate control to limit the inrush current during turn on. Each device is capable of operating over a wide input range from 1.1 V to 5.5 V with very low on-resistance to reduce conduction loss. In the off state, these devices consume very low leakage current to avoid unwanted standby current and save limited input power. The package is a 0.77 mm x 0.77 mm x 0.46 mm wafer level chip scale package, saving space in compact applications. It is constructed using 4 bumps, with a 0.4 mm pitch for manufacturability.

Input Capacitor

A capacitor is recommended to be placed close to the V_{IN} pin to reduce the voltage drop on the input power rail caused by transient inrush current at start-up. A higher input capacitor value can be used to further attenuate the input voltage drop.

Output Capacitor

An output capacitor is recommended to mitigate voltage undershoot on the output pin the moment when the switch is turned off. Undershoot can be caused by parasitic inductance from board traces or intentional load inductances. If load inductances do exist, use of an output capacitor can improve output voltage stability and system reliability. The COUT capacitor should be placed close to the VOUT and GND pins.

EN pin

The GLF71300 / GLF71301 / GLF71306 / GLF71308 can be activated by EN pin high level and the GLF71302 / GLF71303 by EN pin low level. Note that the EN pin has an internal pull-down resistor to help pull the main switch to a known "off state" when no EN signal is applied from an external controller.

Output Discharge Function

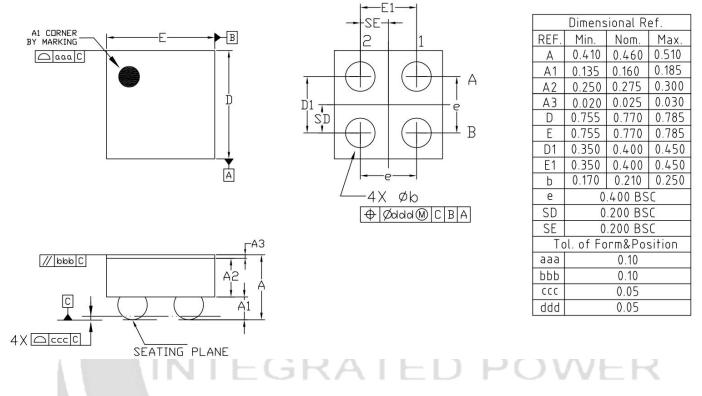
The GLF71301 / GLF71303 / GLF71306 / GLF71308 has an internal discharge N-channel FET switch on the VOUT pin. When EN signal turns the main power FET to an off state, the N-channel switch turns on to discharge an output capacitor quickly.

Board Layout

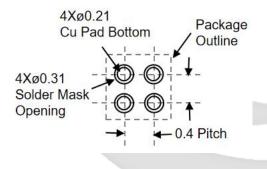
All traces should be as short as possible to minimize parasitic inductance effects. Wide traces for VIN, VOUT, and GND will help reduce voltage drops and parasitic effects during dynamic operation as well as improve the thermal performance at high load current.

► Nano-Current Consumed, I_QSmart[™] Power Load Switch with Slew Rate Control

PACKAGE OUTLINE



Recommended Footprint

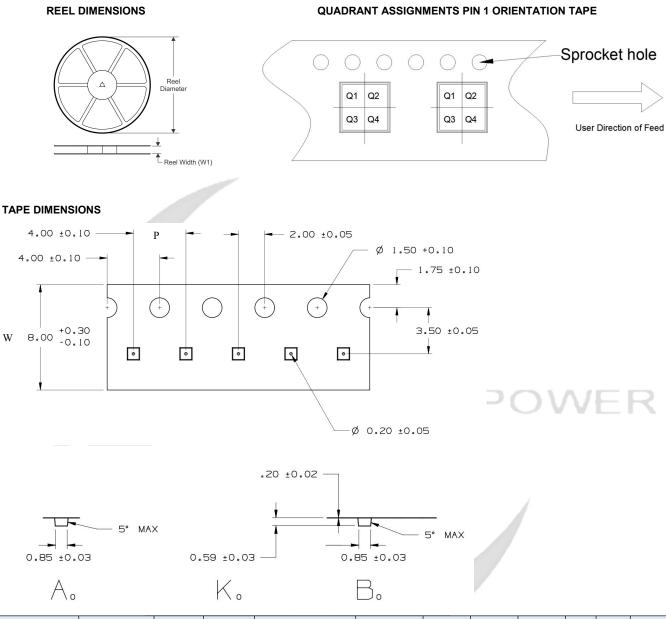


Notes

- 1. ALL DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGRESS)
- 2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
- 3. A3: BACKSIDE LAMINATION

► **Nano-Current Consumed, I**QSmartTM Power Load Switch with Slew Rate Control INTEGRATED POWER

TAPE AND REEL INFORMATION



Device	Package	Pins	SPQ	Reel Diameter (mm)	Reel Width W1	A0	В0	К0	Ρ	w	Pin1
GLF71300	WLCSP	4	4000	180	9	0.85	0.85	0.59	4	8	Q1
GLF71301	WLCSP	4	4000	180	9	0.85	0.85	0.59	4	8	Q1
GLF71302	WLCSP	4	4000	180	9	0.85	0.85	0.59	4	8	Q1
GLF71303	WLCSP	4	4000	180	9	0.85	0.85	0.59	4	8	Q1
GLF71306	WLCSP	4	4000	180	9	0.85	0.85	0.59	4	8	Q1
GLF71308	WLCSP	4	4000	180	9	0.85	0.85	0.59	4	8	Q1

Remark:

A0: Dimension designed to accommodate the component width

B0: Dimension designed to accommodate the component length

C0: Dimension designed to accommodate the component thickness

W: Overall width of the carrier tape

P: Pitch between successive cavity centers

► Nano-Current Consumed, I_QSmart[™] Power Load Switch with Slew Rate Control

SPECIFICATION DEFINITIONS

Document Type	Meaning	Product Status
Target Specification	This is a target specification intended to support exploration and discussion of critical needs for a proposed or target device. Spec limits including typical, minimum, and maximum values are desired, or target, limits. GLF reserves the right to change limits at any time without warning or notification. A target specification in no way guarantees future production of the device in question.	Design / Development
Preliminary Specification	This is a draft version of a product specification. The specification is still under internal review and subject to change. GLF reserves the right to change the specification at any time without warning or notification. A preliminary specification in no way guarantees future production of the device in question.	Qualification
Product Specification	This document represents the anticipated production performance characteristics of the device.	Production

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